

ABSTRACT

Metal structures for ICs and methods for manufacturing the same are described. The metal structures range from small features to large features and are resistant to peeling problems during heat treatments that occur during the manufacturing process. Peeling of the metal structures from the underlying structures or substrates is reduced or prevented. The peeling problems are reduced or prevented by including a capping layer or capping structure over the dielectric layer over the metal structure and then annealing the capping layer or capping structure, thereby enhancing the adhesion of the metal structure to the underlying structure or substrate.

40025.002